In the Specification

On page 58, please replace Table 8 with the following amended Table:

Table 8

Q/Y(cd/A) 8.13 7.95 7.59 7.98 7.98 7.75 8.11 8.24 5.67 5.23 Film thickness (Å) 15 20 15 10 S STRUCTURAL FORMULA (1)-10(4:1)Li₂SiO₃ + LGCHIL001 Second layer V_2O_5 V_2O_5 V_2O_5 $V_2O_5\\$ Charge generation layer 15-0 Mono unit type Film thickness (Å) 15 15 30 15 15 15 15 15 $\text{Li}_2 \text{SiO}_3 + \text{LGCHIL001}$ STRUCTURAL FORMULA (1)-STRUCTURAL FORMULA(1)-Li₂SiO₃ + LGCHIL001 First layer Li_2SiO_3 Li_2SiO_3 $\text{Li}_2 \text{SiO}_3$ Li_2SiO_3 Li_2SiO_3 Li_2SiO_3 10(4:1)10(4:1)Display devices 10 Comp. Ex. 6 Comp. Ex. 1 Comp. Ex. 2 Comp. Ex. 3 Comp. Ex. 4 Comp. Ex. 5 Ex. 3 Ex. 4 Ex. 1 7 Ex.

On page 59, please replace paragraph 1 with the following amended paragraph:

In Example 1, Li₂SiO₃ was deposited at a film thickness of 15 Å to form a charge generation layer 15-0 of a single layer structure. In Examples 2 and 3, Li₂SiO₃ and LGCHIL001 STRUCTURAL FORMULA (1)-10, a hole injection material, were coevaporated to form at the respective film thicknesses charge generation layers 15-0 of a single-layer structure which were composed of mixed layers, respectively. The composition was set at Li₂SiO₃:LGCHIL001 STRUCTURAL FORMULA (1) - 10 = 4:1 (film thickness ratio). In Example 4, a charge generation layer 15-0 was formed with a second layer formed of a mixed layer of Li₂SiO₃:LGCHIL001 STRUCTURAL FORMULA (1) - 10 = 4:1 (film thickness ratio) and stacked over a first layer composed of Li₂SiO₃.